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VS-ST1000C..K

RoHS

COMPLIANT

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Phase Control Thyristors (Hockey PUK Version), 1473 A



PRIMARY CHARACTERISTICS						
I _{T(AV)}	1473 A					
V _{DRM} /V _{RRM}	1200 V, 1400 V, 1600 V, 1800 V, 2000 V, 2200 V, 2400 V					
V _{TM}	1.80 V					
I _{GT}	100 mA					
TJ	-40 °C to +125 °C					
Package	K-PUK (A-24)					
Circuit configuration	Single SCR					

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case K-PUK (A-24)
- High profile hockey PUK
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1473	A			
I _{T(AV)}	T _{hs}	55	°C			
1		2913	A			
I _{T(RMS)}	T _{hs}	25	°C			
1	50 Hz	20.0	- A			
I _{TSM}	60 Hz	21.2				
124	50 Hz	2000	- kA ² s			
1 ² t 60 Hz		1865				
l²√t		20 000	kA²√s			
V _{DRM} /V _{RRM}	Range	1200 to 2400	V			
t _q	Typical	300	μs			
TJ	Range	-40 to +125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 125 °C mA				
	12	1200	1300					
	14	1400	1500					
	16	1600	1700					
VS-ST1000CK	18	1800	1900	100				
	20	2000	2100					
	22	2200	2300					
	24	2400	2500					

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ABSOLUTE MAXIMUM RATINGS	5					
PARAMETER	SYMBOL		TEST CON	DITIONS	VALUES	UNITS
Maximum average on-state current	1	180° conduction, half sine wave		1473 (630)	Α	
at heatsink temperature	I _{T(AV)}	Double side	e (single side) co	ooled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	6540	А
		t = 10 ms	No voltage		20.0	
Maximum peak, one-cycle,		t = 8.3 ms	reapplied		21.2	kA
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		17.0	
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial T _J = T _J maximum	18.1	
	l ² t	t = 10 ms	No voltage		2000	kA ² s
		t = 8.3 ms	reapplied		1865	
Maximum I ² t for fusing	1 - t	t = 10 ms	100 % V _{RRM}		1445	
		t = 8.3 ms	reapplied		1360	
Maximum I²√t for fusing	l²√t	t = 0.1 ms te	o 10 ms, no vol	tage reapplied	20 000	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	I _{T(AV)}), T _J = T _J maximum	0.950	v
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J$ maximum			v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	I _{T(AV)}), T _J = T _J maximum	0.283	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			0.265	mΩ
Maximum on-state voltage drop	V _{TM}	$I_{pk} = 3000 \text{ A}, T_J = 125 \text{ °C}, t_p = 10 \text{ ms sine pulse}$		1.80	V	
Maximum holding current	Ι _Η	T 05 %0	$T_{,1} = 25 \text{ °C}$, anode supply 12 V resistive load			
Typical latching current	١L	$I_{\rm J} = 25^{-1}$ C,	anoue supply 1		1000	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \leq 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.9	
Typical turn-off time	tq	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	300	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA



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TRIGGERING							
PABAMETER	SYMBOL	TE	TEST CONDITIONS			UNITS	
FARAMETER	STIVIDOL		STCONDITIONS	TYP.	MAX.		
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	, t _p ≤ 5 ms	1	6	w	
Maximum peak average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	, f = 50 Hz, d% = 50	C.	3	vv	
Maximum peak positive gate current	I _{GM}			3	.0	А	
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum,	, t _p ≤ 5 ms	2	0	v	
Maximum peak negative gate voltage	-V _{GM}						
		T _J = -40 °C		200	-		
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger/	100	200	mA	
		T _J = 125 °C	current/voltage are the lowest	50	-		
		T _J = -40 °C	value which will trigger all units	1.4	-		
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	12 V anode to cathode applied	1.1	3.0	V	
		T _J = 125 °C		0.9	-		
DC gate current not to trigger	I _{GD}	T ₁ = T ₁ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any	10		mA	
DC gate voltage not to trigger	V _{GD}	rj = rjinaximum	unit with rated V _{DRM} anode to cathode applied	0.25		V	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating temperature range	TJ		-40 to +125	0		
Maximum storage temperature range	T _{Stg}		-40 to +150	C		
Maximum thermal resistance,	kimum thermal resistance,		0.042			
junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.021	к/w		
Maximum thermal resistance,	Р	DC operation single side cooled	0.006	~~vv		
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500	Ν		
			(2500)	(kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet	K-PUK (A	-24)		

$\Delta \mathbf{R}_{thJC}$ CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAF	R CONDUCTION	TEST CONDITIONS	UNITS
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE			TEST CONDITIONS	UNITS
180°	0.003	0.003	0.002	0.002		
120°	0.004	0.004	0.004	0.004		
90°	0.005	0.005	0.005	0.005	$T_J = T_J$ maximum	K/W
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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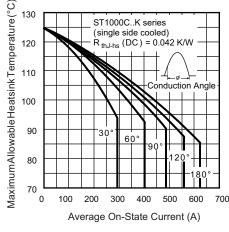


Fig. 1 - Current Ratings Characteristics

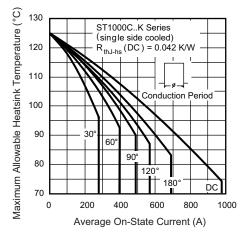


Fig. 2 - Current Ratings Characteristics

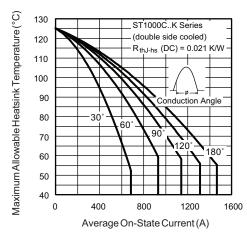


Fig. 3 - Current Ratings Characteristics

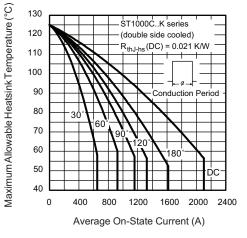


Fig. 4 - Current Ratings Characteristics

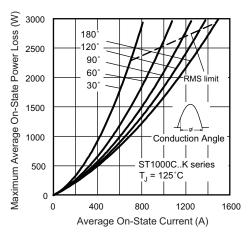


Fig. 5 - On-State Power Loss Characteristics

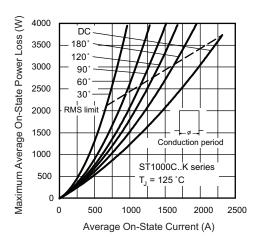


Fig. 6 - On-State Power Loss Characteristics

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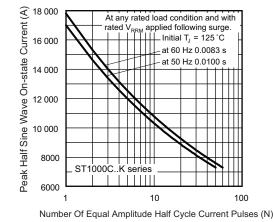
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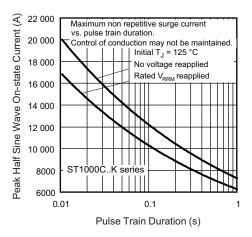
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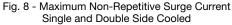
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Single and Double Side Cooled





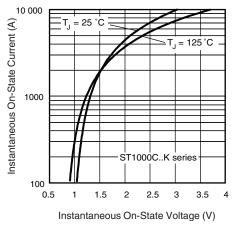
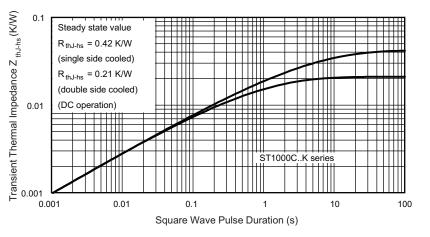
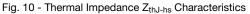


Fig. 9 - On-State Voltage Drop Characteristics





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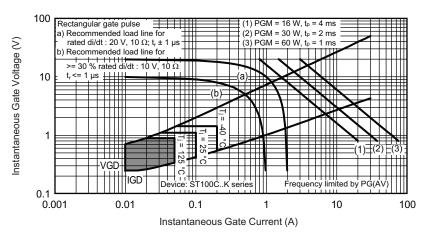


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	100	0	с	24	к	1	-	
		2	3	4	5	6	7	8	9	
	1 -		-	niconduc	ctors pro	oduct				
	2 - 3 -		ristor ential n	art numt	her					
	4 -		-	er grade						
	5 -	C =	cerami	c PUK						
	6 -	Vol	age coo	de x 100	= V _{RRN}	₁ (see V	oltage F	Ratings	table)	
	7 -	K =	PUK ca	ase K-Pl	JK (A-24	4)				
	8 -	0 =	eyelet t	erminals	s (gate a	and auxi	liary ca	thode u	nsolder	ed leads)
		1 =	fast-on	terminal	ls (gate	and aux	kiliary ca	athode (unsolde	red leads)
		2 =	eyelet t	erminals	s (gate a	and auxi	liary ca	thode s	oldered	leads)
		3 =	fast-on	terminal	ls (gate	and aux	kiliary ca	athode	soldered	l leads)
	9 -	Crit	ical dV/	dt: • nor	ne = 500) V/µs (s	standar	d select	ion)	
				• L =	1000 V	/µs (spe	ecial sel	ection)		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			

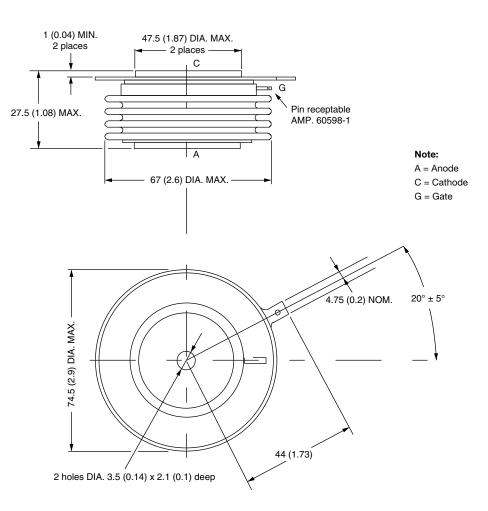


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K-PUK (A-24)

DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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